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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/710,488	07/14/2004	Henry Chung	10304-US-PA	4487
31561	7590 12/07/2005		EXAMINER	
ЛАNQ CHY	YUN INTELLECTUAL PI	AHMED, SHAMIM		
7 FLOOR-1,			ART UNIT	PAPER NUMBER
ROOSEVELT	Γ ROAD, SECTION 2		ART ONT	- TATER NOMBER
TAIPEI, 100			1765	
TAIWAN			DATE MAILED: 12/07/2009	5

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
	10/710,488	CHUNG ET AL.			
Office Action Summary	Examiner	Art Unit			
	Shamim Ahmed	1765			
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address			
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period wa  - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be time vill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	ely filed the mailing date of this communication.  O (35 U.S.C. § 133).			
Status					
1) Responsive to communication(s) filed on 14 Ju	uly 2004.				
2a) This action is <b>FINAL</b> . 2b) ⊠ This	action is non-final.				
3) Since this application is in condition for allowar	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is				
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims					
<ul> <li>4)  Claim(s) 1-22 is/are pending in the application.</li> <li>4a) Of the above claim(s) is/are withdray</li> <li>5)  Claim(s) is/are allowed.</li> <li>6)  Claim(s) 1-22 is/are rejected.</li> <li>7)  Claim(s) is/are objected to.</li> <li>8)  Claim(s) are subject to restriction and/or</li> </ul>	vn from consideration.				
Application Papers					
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 14 July 2005 is/are: a) ☐ Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) ☐ The oath or declaration is objected to by the Examine	☑ accepted or b)☐ objected to be drawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).			
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list of	s have been received. s have been received in Application ity documents have been received (PCT Rule 17.2(a)).	on No ed in this National Stage			
Attachment(s)  1) Notice of References Cited (PTO-892)	A) [] Intention Commercia	(DTO 412)			
<ul> <li>1) Notice of References Cited (PTO-892)</li> <li>2) Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)         <ul> <li>Paper No(s)/Mail Date</li> </ul> </li> </ul>	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal Pa	•			

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### **DETAILED ACTION**

## Claim Objections

1. Claim 1 is objected to because of the following informalities: in line 6, the phrase "to exposed" should have been "to expose". Appropriate correction is required.

## Claim Rejections - 35 USC § 112

- 2. The following is a quotation of the first paragraph of 35 U.S.C. 112:
  - The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.
- 3. Claims 1-22 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the enablement requirement. The claim(s) contains subject matter, which was not described in the specification in such a way as to enable one skilled in the art to which it pertains, or with which it is most nearly connected, to make and/or use the invention. Specification only discloses etching the (hard) mask layer using a patterned photoresist layer but does not provide any clear explanation how to form the plurality of micro-trenches that one of skilled in the art reasonable practices the invention.
- 4. The following is a quotation of the second paragraph of 35 U.S.C. 112:

  The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 5. Claim 1 recites the limitation "due to the trenching effect" in lines 8-9. There is insufficient antecedent basis for this limitation in the claim.
- 6. Claim 10 recites the limitation "due to the trenching effect "in lines 7-8. There is insufficient antecedent basis for this limitation in the claim.

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7. Claim 19 recites the limitation "the exposed region" in line 8. There is insufficient antecedent basis for this limitation in the claim.

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8. Claims 1-22 are now free of art and the closest prior art Tsai et al (6,878,646) teach a process for reducing the critical dimension of a hard mask but fail to teach a process of reducing pattern pitch on a substrate including the steps of etching the hard mask layer using a patterned photoresist layer, while a residual hard mask layer remains in the exposed region and a plurality of micro-trenches are formed at the edges of the residual hard mask layer I the exposed region as claimed.

### Conclusion

9. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Tamura (US 2003/0222287) and Zheng (6,475,922) discloses a process of etching a substrate comprises polysilicon, wherein hard mask is used to control the etching process without micro-trenching.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shamim Ahmed whose telephone number is (571) 272-1457. The examiner can normally be reached on M-Thu (7:00-5:30) Every Friday Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G. Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Shamim Ahmed Primary Examiner Art Unit 1765

SA December 3, 2005